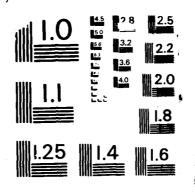
STRENGTH AND STRUCTURE OF GA(1-X)IN(X)AS ALLOYS(U) OHIO STATE UNIV RESEARCH FOUNDATION COLUMBUS K T FABER ET AL 15 APR 87 AFOSR-TR-87-8735 F49620-85-C-8129 F/G 7/2 AD-A181 167 171 UNCLASSIFIED NL



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Strength and Structure of Ga1-	_x In _x As Alloys	<u> </u>		<u> </u>	
12. PERSONAL AUTHOR(S) Katherine T. Faber and John 1	P. Hirth				
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RF Project 764977/717636 Quarterly Report

AFOSR-TH- 87-0735

STRENGTH AND STRUCTURE of $Ga_{1-x}IN_x$ AS ALLOYS

K. T. Faber Approved for public release; Department of Ceramic Engineering J. P. Hirth Department of Metallurgical Engineering

For the Period January 1, 1987 - March 31, 1987

AIR FORCE OFFICE OF SCIENTIFIC RESEARCH Building 410 Bolling AFB, D.C. 20332-6448

Contract No. F49620-85-C-0129

April 1987



The Ohio State University Research Foundation

> 1314 Kinnear Road Columbus, Ohio 43212

AIR FORCE OFFICE OF SCIENTIFIC RESEARCH (AFSC)

The strengthening effect of gallium arsenide by indium additions is under examination. Interpretation of high temperature hardness results of In-free and In-containing GaAs suggests that the intermediate temperature hardening of these materials may be sufficient to reduce dislocation densities by two orders of magnitude during growth. The second quarterly report describes the most recent mechanical tests and electron microscopy in this study to better understand the solid-solution strengthening in these systems.

(1) Progress

Compression tests on LEC grown semi-insulating undoped and In-doped GaAs single crystals have been completed in the [123] orientation in the temperature range 700 to 1100°C. The [123] orientation allows deformation via a single slip system. The In-doped materials had an In concentration of 2x10²⁰ cm⁻³. For both materials, the linear region of the stress-strain curve results in a lower-than-anticipated elastic modulus, indicating the occurrence of micro-creep. The slope is significantly smaller for undoped materials, suggesting a higher creep resistance for In-doped materials.

Both undoped and In-doped materials showed the presence of an easy glide region in this single slip orientation. However, the critical resolved shear stress (CRSS) for the In-doped material was nearly twice that of the undoped material. This observed increase in the resistance to glide is sufficient to eliminate dislocations in the growth of large diameter crystals. Values of the CRSS are weakly temperature

A-1

dependent, consistent with the solid solution strengthening model proposed.

In Stage III of the deformation, higher stress values for the onset of dynamic recovery show that dislocation climb is slowed by the Indium doping.

Transmission electron microscopy studies of deformed Indoped and undoped [100] GaAs are complete. Specimens deformed at 900 and 1100°C show complex defect structures due to multiple slip. Perfect as well as partial dislocations forming dislocation networks have been observed. However, dislocation loops, prevalent in specimens deformed at 700°C, were rare in the 1100°C samples. A detailed analysis of the dislocation structures and their interaction mechanism is in progress. An estimate of the stacking fault energy will be performed on these specimens by measuring the width of the partial dislocations in the deformed specimens. Furthermore, TEM studies of deformed materials in the single slip orientation, [123], will be performed.

- (2) Special equipment purchased or constructed None.
- (3) Changes in key personnel None.

(4) Substantive information derived from meetings

Materials for study are continuing to be supplied by Dr.

Noel Thomas of Westinghouse R&D Center. Discussions with Dr.

Thomas' group take place on a bimonthly basis.

Undoped GaAs grown by the Bridgman technique has been

ordered from Crystal Specialties, Inc. for comparative studies. In addition, Dr. Arati Prabhakar from DARPA has requested high purity Bridgman crystals from Bell Laboratories for our studies.

(5) Problems of concern
None.

(6) Fiscal Status

- (a) Amount currently provided for contract: \$289,268.00
- (b) Expenditures and commitments to 12/31/86: \$165,387.28 March financial statement attached.
- (c) Amount needed to complete work: \$123,880.72
- (d) Estimated date of completion: 8/31/87

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SALARIES AND WAGES - RELEASE TIME SALARIES AND WAGES - ROTARY TIME FRINGES - RELEASE TIME FRINGES - ROTARY TIME	27.868.00 108.942.00 4.882.00 24.707.00	2,358,40 4,510,00 406,82 678,90	17.297.56 63.276.74 3.082.58 9.373.25	3,537.60 13,530.00 495.26 1,854.97	7.032.84 32.135.26 1.304.16 13.478.78
TOTAL PERSONNEL CUSTS	166.399.00	7.954.12	43.030.13	19-417-83	53,951.04
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TOTAL DIRECT COSTS	203.294.00	6.010.97	117,472,21	21,661.23	64,150.56
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